# MSKSEMI 美森科













**ESD** 

MOV

3DT

PLED

# SS5150B-MS THRU SS5200B-MS

**Product specification** 



# **SS5150B-MS THRU SS5200B-MS**

#### **Features**

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability
  Classification Rating 94V-O

#### **MECHANICAL DATA**

- Case: SMB/DO-214AA, Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.093 grams (approx.)

#### **Reference News**

# DO-214AA/SMB Schematic Diagram

### **Marking**

SS5150B-MS	SS5200B-MS	
SS5150	SS5200	

# Maximum Ratings and Electrical Characteristics T<sub>A</sub> = 25 ℃ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

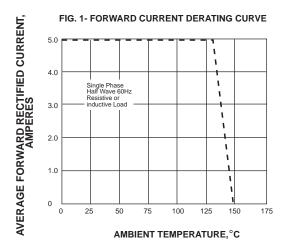
Characteristic	Symbol	SS5150B-MS	SS5200B-MS	Unit
Maximum repetitive peak reverse voltage	VRRM	150 200		Volts
Maximum RMS voltage	VRMS	105	150	Volts
Maximum DC blocking voltage	VDC	150	200	Volts
Maximum average forward rectified current at TL(see fig.1)	l(AV)	5.0		Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	Ігѕм	15	50.0	Amps
Maximum instantaneous forward voltage at 5.0A	VF	0.85	0.95	Volts
Maximum DC reverse current TA=25℃		0.2		- mA
at rated DC blocking voltage T <sub>A</sub> =100℃	R	2	2.0	
Typical junction capacitance (NOTE 1)	Cı	C <sub>J</sub> 200		pF
Typical thermal resistance (NOTE 2)	RθJA	50.0		°C/W
Operating junction temperature range	TJ,	-50 to +150		$^{\circ}$ C
Storage temperature range	Тѕтс	-50 to +150		$^{\circ}\!\mathbb{C}$

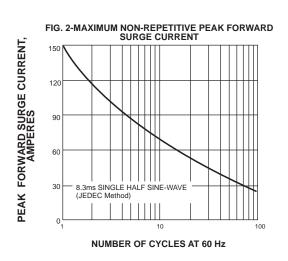
 $\textbf{Note:} 1. \\ \text{Measured at 1MHz and applied reverse voltage of 4.0V D.C.}$ 

2.P.C.B. mounted with 0.2x0.2"(5.0x5.0mm) copper pad areas



#### RATINGS AND CHARACTERISTIC CURVES SS5150B-MS THRU SS5200B-MS







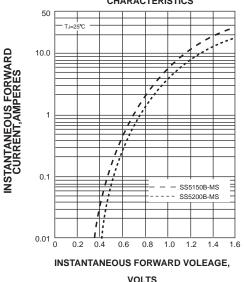
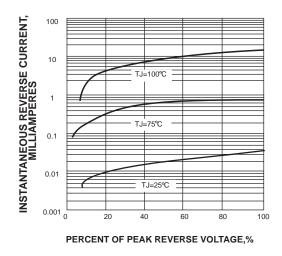
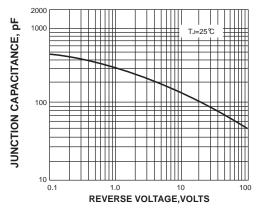
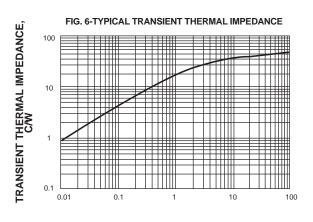


FIG. 4-TYPICAL REVERSE CHARACTERISTICS



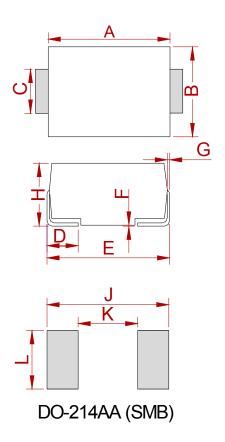
#### FIG. 5-TYPICAL JUNCTION CAPACITANCE







# PACKAGE MECHANICAL DATA



	Dimensions			
Ref.	Millimeters		Inches	
	Min.	Max.	Min.	Max.
Α	4.25	4.75	0.167	0.187
В	3.30	3.94	0.130	0.155
С	1.85	2.21	0.073	0.087
D	0.76	1.52	0.030	0.060
Е	5.08	5.59	0.200	0.220
F	0.051	0.203	0.002	0.008
G	0.15	0.31	0.006	0.012
Н	2.11	2.44	0.083	0.096
J	6.80		0.270	
K		2.60		0.100
L	2.40		0.090	

## **REEL SPECIFICATION**

P/N	PKG	QTY
SS5150B-MS THRU SS5200B-MS	DO-214AA(SMB)	3000

# SS5150B-MS THRU SS5200B-MS

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